ocket No.: 060188-0670

**PATENT** 

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Customer Number: 20277

Taiji NODA

Confirmation Number: 8100

Application No.: 10/676,877

Group Art Unit: 2822

Filed: October 02, 2003

Examiner: TRINH, Michael Manh

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

## **INFORMATION DISCLOSURE STATEMENT**

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

This Information Disclosure Statement is being filed more than three months after the U.S. filing date and after the mailing date of a Final Rejection or Notice of Allowance, but before payment of the Issue Fee.

## REQUEST TO CONSIDER REFERENCES AFTER CLOSE OF PROSECUTION AND BEFORE PAYMENT OF ISSUE FEE

The undersigned hereby requests consideration and entry of this Information Disclosure Statement and accompanying references under 37 CFR 1.97(d).

Please charge the processing fee under 1.17(p) of \$180.00 to Deposit Account 500417.

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CERTIFICATION PARAGRAPH

The undersigned certifies that each item of information contained in this Information

Disclosure Statement was first cited in a communication from a foreign patent office in a

counterpart foreign application not more than three months prior to the filing of this Information

Disclosure Statement as described in 37 CFR 1.97(e)(1).

Each English language reference was cited in a corresponding foreign application search

report and its relevance discussed therein. A copy of the foreign search report is attached for the

Examiner's information.

Please charge any shortage in fees due in connection with the filing of this paper,

including extension of time fees, to Deposit Account 500417 and please credit any excess fees to

such deposit account.

Respectfully submitted,

McDERMOTT WIZL & EMERY LLP

Michael E. Fogarty

Registration No. 36,139

600 13th Street, N.W. Washington, DC 20005-3096

Phone: 202.756.8000 MEF:mfm

Facsimile: 202.756.8087

Date: May 19, 2006

as our correspondence address.

Please recognize our Customer No. 20277

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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.